NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI MRW2020** is a high performance common base RF power transistor intended for 28V operation across the 1 to 2.3 GHz frequency range.

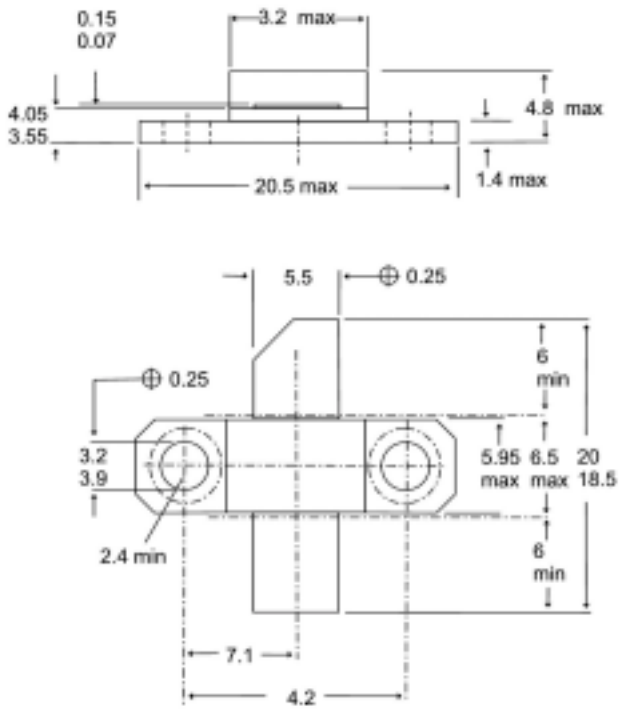
FEATURES:

- Gain: 5.2 dB Min. at 20 W
- Output Power: 20 W
- Diffused Ballast Resistors
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	4.0 A
V_{CES}	50 V
V_{EBO}	3.5 V
P_{DISS}	60 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	3.0 °C/W

PACKAGE STYLE .250X.300 2L FLG



CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I_C = 160 mA	50	---	---	V
BV_{EBO}	I_E = 2.0 mA	3.5	---	---	V
I_{CBO}	V_{CB} = 28 V	---	---	2.0	A
h_{FE}	V_{CE} = 5.0 V I_C = 800 mA	10	---	100	---
C_{ob}	V_{CB} = 28 V f = 1.0 MHz	---	---	24	pF
G_{PB}	V_{CC} = 28 V P_{OUT} = 20 W f = 2.0 GHz	5.2	---	---	dB
η_C		40	---	---	%
Ψ	V_{CC} = 28 V f = 2.0 GHz Load VSWR = ∞:1, All Phase Angles	No Degradation in Output Power			

Specifications are subject to change without notice.